



60V P-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

Product Summary

BV _{DSS}	R _{DS(ON)}	I _D T _C = +25°C
-60V	18mΩ @ V _{GS} = -10V	-60A
-60 V	26mΩ @ V _{GS} = -4.5V	-50A

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- DC-DC Converters
- Load Switch

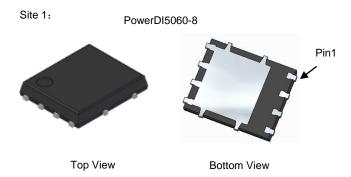
Features and Benefits

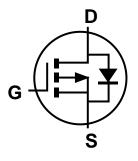
- 100% Unclamped Inductive Switch (UIS) Test in Production
- Low R_{DS(ON)} Minimizes On State Losses
- Low Input Capacitance
- Fast Switching Speed
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMP6018LPSQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

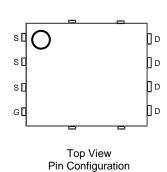
Mechanical Data

- Case: PowerDI[®]5060-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 <a>©3
- Weight: 0.097 grams (Approximate)



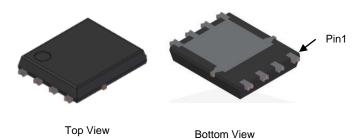


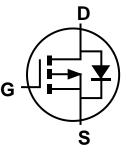
Internal Schematic



Site 2:

PowerDI5060-8 (SWP) (Type UX)





Internal Schematic

Top View Pin Configuration

PowerDI is a registered trademark of Diodes Incorporated.



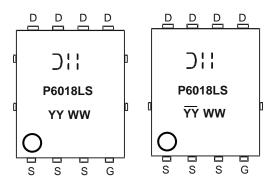
Ordering Information (Note 4)

Part Number	Case	Packaging
DMP6018LPSQ-13	PowerDI5060-8	2,500 / Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



)¦¦ = Manufacturer's Marking
P6018LS = Product Type Marking Code
YYWW = Date Code Marking
YY or YY = Year (ex: 20 = 2020)
WW = Week (01 to 53)

Maximum Ratings (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			VDSS	-60	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current, $V_{GS} = -10V$ (Note 6) Steady $T_{C} = +25^{\circ}C$ State $T_{C} = +70^{\circ}C$			lD	-60 -48	А
Maximum Continuous Body Diode Forward Current			Is	-60	Α
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I _{DM}	-240	Α
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)			I _{SM}	-240	Α
Avalanche Current, L = 0.3mH			las	-47	A
Avalanche Energy, L = 0.3mH			Eas	331	mJ

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	PD	2.6	W
Thermal Resistance, Junction to Ambient (Note 5)		Rеја	50	°C/W
Total Power Dissipation (Note 6)	T _C = +25°C	P _D	113	W
Thermal Resistance, Junction to Case (Note 6)		Rejc	1.1	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.

6. Thermal resistance from junction to soldering point (on the exposed drain pad).



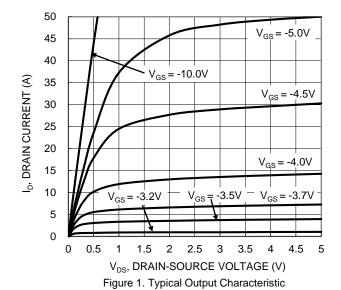
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	-60	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$
Zero Gate Voltage Drain Current	IDSS	_	_	-1	μΑ	V _{DS} = -60V, V _{GS} = 0V
Gate-Source Leakage	Igss	_	_	±100	nA	$V_{GS} = \pm 20V$, $V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	Vgs(th)	-1.5	_	-2.5	V	$V_{DS} = V_{GS}$, $I_D = -250\mu A$
Static Drain-Source On-Resistance	D	_	13	18	mΩ	V _{GS} = -10V, I _D = -17A
Static Drain-Source On-Resistance	RDS(ON)	_	22	26	11122	$V_{GS} = -4.5V, I_{D} = -5A$
Diode Forward Voltage	V _{SD}	_	-0.76	-1.0	V	V _{GS} = 0V, I _S = -17A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	Ciss	_	3505	_		V _{DS} = -30V, V _{GS} = 0V, f = 1MHz
Output Capacitance	Coss	_	516	_	pF	
Reverse Transfer Capacitance	Crss	_	200	_		
Gate Resistance	R _G	_	9.1	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$
Total Gate Charge (V _{GS} = -4.5V)	Qg	_	7.1	_		V _{DS} = -30V, I _D = -10A
Total Gate Charge (Vgs = -10V)	Qg	_	13.7	_	~C	
Gate-Source Charge	Qgs	_	1.8	_	nC	
Gate-Drain Charge	Q _{gd}		3.5	_		
Turn-On Delay Time	t _{D(ON)}		3.9	_		$V_{DD} = -30V$, $V_{GS} = -10V$, $I_{D} = -10A$, $R_{G} = 2.5\Omega$
Turn-On Rise Time	t _R		6.7	_		
Turn-Off Delay Time	tD(OFF)		16.0	_	ns	
Turn-Off Fall Time	t _F	_	7.2	_		
Body Diode Reverse Recovery Time	trr	_	32	_	ns	1 470 37/34 4000/55
Body Diode Reverse Recovery Charge	Qrr	_	28	_	nC	$-I_S = -17A$, di/dt = 100A/ μ s

Notes:

^{7.} Short duration pulse test used to minimize self-heating effect. 8. Guaranteed by design. Not subject to product testing.





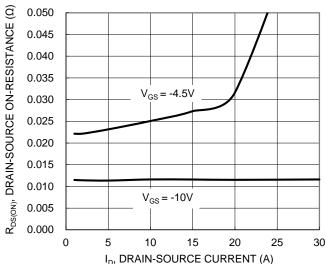


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

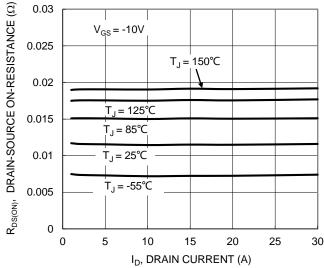


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

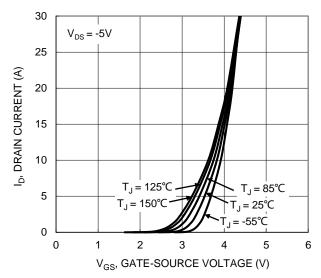


Figure 2. Typical Transfer Characteristic

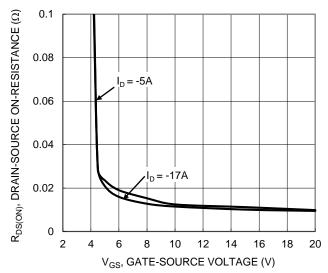


Figure 4. Typical Transfer Characteristic

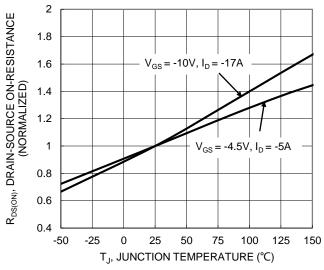


Figure 6. On-Resistance Variation with Temperature



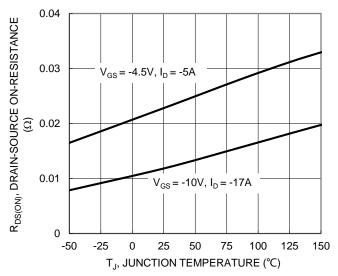


Figure 7. On-Resistance Variation with Temperature

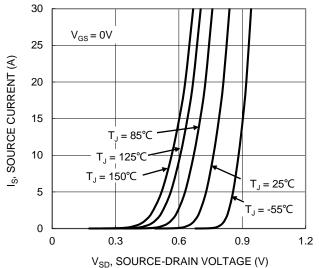


Figure 9. Diode Forward Voltage vs. Current

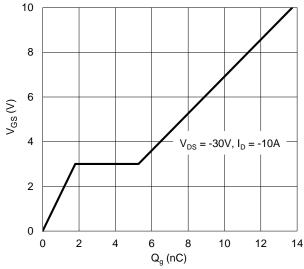


Figure 11. Gate Charge

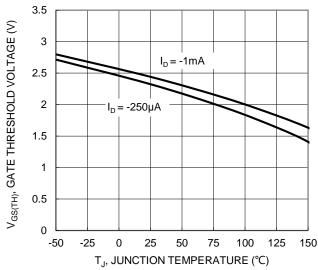


Figure 8. Gate Threshold Variation vs. JunctionTemperature

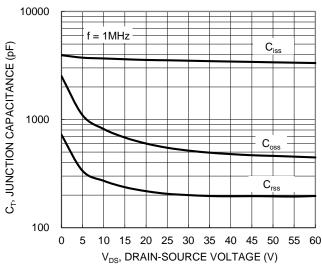
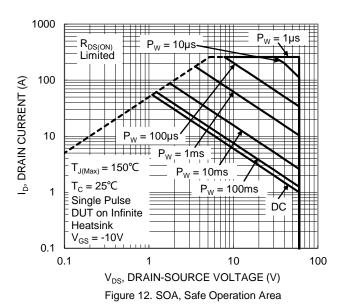


Figure 10. Typical Junction Capacitance





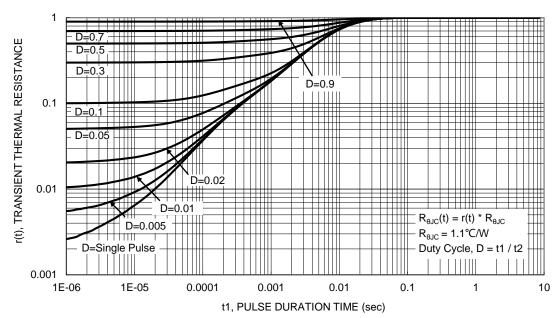


Figure 13. Transient Thermal Resistance

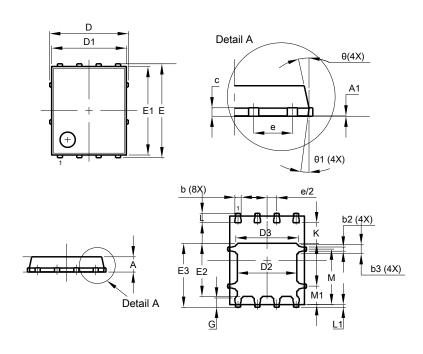


Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

Site 1:

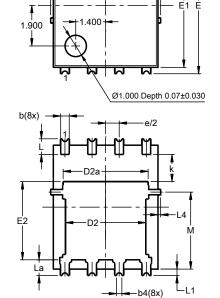
PowerDI5060-8



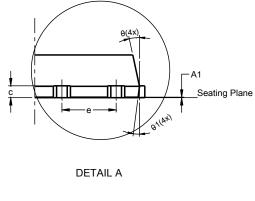
PowerDI5060-8				
Dim	Min	Max	Тур	
Α	0.90	1.10	1.00	
A 1	0.00	0.05	-	
b	0.33	0.51	0.41	
b2	0.200	0.350	0.273	
b3	0.40	0.80	0.60	
С	0.230	0.330	0.277	
D		5.15 BSC		
D1	4.70	5.10	4.90	
D2	3.70	4.10	3.90	
D3	3.90	4.30	4.10	
Е	(6.15 BSC	;	
E1	5.60	6.00	5.80	
E2	3.28	3.68	3.48	
E3	3.99	4.39	4.19	
е	1.27 BSC			
G	0.51	0.71	0.61	
K	0.51	-	-	
L	0.51	0.71	0.61	
L1	0.100	0.200	0.175	
M	3.235	4.035	3.635	
M1	1.00	1.40	1.21	
Θ	10°	12°	11°	
Θ1	6°	8°	7°	
All Dimensions in mm				

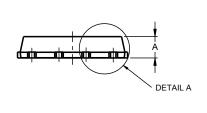
Site 2:

PowerDI5060-8 (SWP) (Type UX)



-D1





PowerDI5060-8 (SWP)				
	(Туре	UX)		
Dim	Min	Max	Тур	
Α	0.90	1.10	1.00	
A1	0	0.05		
b	0.30	0.50	0.41	
b2	0.20	0.35	0.25	
b4	().25REF	=	
С	0.230	0.330	0.277	
D	5	.15 BS(2	
D1	4.70	5.10	4.90	
D2	3.56	3.96	3.76	
D2a	3.78	4.18	3.98	
Е	6	.40 BS0	\circ	
E1	5.60	6.00	5.80	
E2	3.46	3.86	3.66	
E2a	4.195	4.595	4.395	
е	1	.27BSC)	
k	1.05			
L	0.635	0.835	0.735	
La	0.635	0.835	0.735	
L1	0.200	0.400	0.300	
L1a	0	.050RE	F	
L4	0.025	0.225	0.125	
М	3.205	4.005	3.605	
θ	10°	12°	11°	
θ1	6°	8°	7°	
All Dimensions in mm				

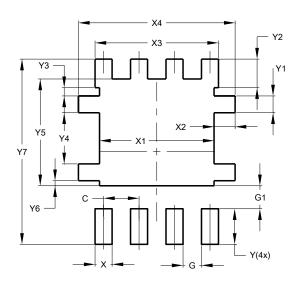


Suggested Pad Layout

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Site 1:

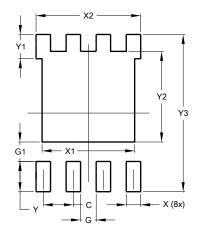
PowerDI5060-8



Dimensions	Value (in mm)
С	1.270
G	0.660
G1	0.820
Χ	0.610
X1	4.100
X2	0.755
Х3	4.420
X4	5.610
Υ	1.270
Y1	0.600
Y2	1.020
Y3	0.295
Y4	1.825
Y5	3.810
Y6	0.180
Y7	6.610

Site 2:

PowerDI5060-8 (SWP) (Type UX)



Dimensions	Value (in mm)
С	1.270
G	0.660
G1	0.820
Х	0.610
X1	4.100
X2	4.420
Υ	1.270
Y1	1.020
Y2	3.810
Y3	6.610



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